1.2.3 <u>Case outlines</u>. The case outlines should be designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
A <u>4</u> /	GDFP5-F14 or CDFP6-F14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
Z	GDFP1-G14	14	Flat pack with gullwing leads

1.3 Absolute maximum ratings.

Supply voltage range :	
Device types 01, 02, 03, and 04	. ±22 V dc <u>5</u> /
Device types 05 and 06	. 36 V or ±18 V <u>5</u> /
Input voltage range:	
Device types 01, 02, 03, and 04	. ±20 V dc <u>6</u> /
Device types 05 and 06	$\cdot -V_{CC} - 0.3 \text{ V to } +V_{CC}$
Differential input voltage range	.±30 V dc <u>7</u> /
Input current range:	
Device types 01 and 02	0.1 mA to +10 mA
Device types 03, 04, 05, and 06	
Storage temperature range	65°C to +150°C
Output short-circuit duration	. Unlimited <u>8</u> /
Lead temperature (soldering, 60 seconds)	. +300°C
Junction temperature (T _J)	. +175°C <u>9</u> /
Thermal resistance, junction-to-case (θ_{JC}) :	
Cases A, C, D, and Z	. See MIL-STD-1835

1.4 Recommended operating conditions.

Supply voltage range:	
Device types 01, 02, 03, and 04	\pm 5 V dc to \pm 20 V dc
Device types 05 and 06	\pm 5 V dc to +30 V dc
Ambient temperature range (T _A)	-55°C to +125°C

4/ Inactive package case outline.

5/ Voltages in excess of these may be applied for short-term tests if voltage difference does not exceed 44 volts (36 volts for device types 05 and 06).

<u>6</u>/ For device types 01 through 04, for supply voltages less than ±20 V dc, the absolute maximum input voltage is equal to the supply voltage. For device types 05 and 06, for supply voltages differences of less than 36 V, the absolute maximum input voltage is equal to the supply voltage.

7/ The differential input voltage range should not exceed the supply voltage range.

8/ Short circuit may be to ground or either supply. Rating applies to +125°C case temperature or +75°C ambient temperature.

<u>9</u>/ For short term test (in the specific burn-in and life test configuration when required and up to 168 hours maximum) $T_J = +275^{\circ}C$.

1.5 Power and thermal characteristics.

Case outlines	Maximum allowable power	Maximum	Maximum
	dissipation	θJC	θja
A, D	350 mW at T _A = +125°C	60°C/W	140°C/W
С	400 mW at T _A = +125°C	35°C/W	120°C/W
Z	350 mW at T _A = +125°C	25°C/W	176°C/W still air
			116°C/W 500 LFPM

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications, standards, and handbooks</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard for Microelectronics. MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this document and the references cited herein the text of this document shall takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).

3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.3.2 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request upon request.

3.3.3 <u>Case outlines</u>. The case outlines shall be as specified in 1.2.3.

3.3.4 Packaging and sealing material. Package and sealing material shall be in accordance with MIL-PRF-38535.

3.4 Lead material and finish. Lead material and finish shall be in accordance with MIL-PRF-38535.

3.5 <u>Electrical performance characteristics</u>. The following electrical performance characteristics are as specified in table I, and apply over the full ambient operating temperature range of -55°C to +125°C and for supply voltages as follows. Unless otherwise specified, source resistance (R_S) shall be 50 Ω for all tests.

Device types 01, 02, 03, and 04 will have a dual power supply with $\pm V_{CC}$ (min) at ± 5 V and $\pm V_{CC}$ (max) at ± 20 V. Device types 05 and 06 will have a single power supply with $\pm V_{CC}$ (min) at ± 5 V and $\pm V_{CC}$ (max) at ± 30 V.

3.5.1 Instability oscillations. The devices shall be free of oscillations when operated in the test circuits of this specifications.

3.6 <u>Electrical test requirements</u>. Electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 <u>Microcircuit group assignment</u>. The devices covered by this specification shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

Test	Symbol	Conditions -55°C ≤ T _A ≤ +125°C see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Input offset voltage	VIO	<u>1/</u>	1	01,02, 04,05		±5	mV
				03		±3	
				06		±2	
			2,3	01,02, 04		±6	
				03		±5	-
				05		±7	
				06		±4	-
Input offset voltage temperature sensitivity	ΔV _{IO} / ΔT		2	01,02, 04		±25	μV/°C
				03		±20	
				05,06		±30	
			3	01,02, 04		±25	-
				03		±20	
				05,06		±30	

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Input offset current	ΙΟ	R _S = 50 Ω <u>1</u> /	1,2	01,02		±25	nA
				03,05		±30	
				04		±75	
				06		±10	
			3	01,02, 03,05		±75	-
				04		±150	
				06		±30	-
Input offset current temperature sensitivity	ΔΙ _{ΙΟ} / ΔΤ		2	01,02, 03		±200	pA/°C
				04		±500	
				05,06		±400	
			3	01,02		±400	-
				03		±500	
				04		±1000	
				05,06		±700	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Lir	nits	Unit						
		unless otherwise specified			Min	Max							
Input bias current	+I _{IB}	R _S = 20 kΩ <u>1</u> /	1,2	01,02	-0.1	100	nA						
				03	-200	+0.1							
				04	-250	+0.1							
				05	-150	+0.1							
				06	-50	+0.1							
									3	01,02	-0.1	325	
								03	-325	+0.1			
									04	-400	+0.1		
						05	-300	+0.1					
				06	-100	+0.1							
	-I _{IB}		1,2	01,02	-0.1	100							
				03	-200	+0.1							
				04	-250	+0.1							
				05	-150	+0.1							
				06	-50	+0.1							

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type		mits	Unit
		unless otherwise specified		04.00	Min	Max	
Input bias current	-I _{IB}	$R_S = 20 k\Omega $ <u>1</u> /	3	01,02	-0.1	325	nA
				03	-325	+0.1	-
				04	-400	+0.1	
				05	-300	+0.1	
				06	-100	+0.1	
Power supply rejection ratio	+PSRR	+V _{CC} = 10 V, -V _{CC} = -20 V	1,2,3	01,02, 03,04		±100	μV/V
		+V _{CC} = 30 V to 5 V		05,06		±100	
	-PSRR	+V _{CC} = 20 V, -V _{CC} = -10 V		01,02, 03,04		±100	
Input voltage common mode rejection	CMR	V _{CM} = 30 V <u>2</u> /	1,2,3	01,02, 03,04	76		dB
		V _{CM} = 28 V <u>2</u> /		05,06	76		
Output short-circuit current (for positive	I _{OS} (+)	$\pm V_{CC} = \pm 15 \text{ V}, \qquad \underline{3}/$	1,2	01,02	-55		mA
output)		t ≤ 25 ms, only one amplifier shorted to GND at one time		03,04	-80		
		$\pm V_{CC} = 30 \text{ V}, \qquad \underline{3}/$ t $\leq 25 \text{ ms, only one}$ amplifier shorted to GND at one time		05,06	-70		
		$\pm V_{CC} = \pm 15 \text{ V}, \qquad \underline{3}/$	3 <u>4</u> /	01,02	-75		
		t ≤ 25 ms, only one amplifier shorted to GND at one time		03,04	-80		
		$\pm V_{CC}$ = 30 V, <u>3</u> / t \leq 25 ms, only one amplifier shorted to GND at one time		05,06	-70		

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Limits		Unit
		unless otherwise specified			Min	Max	
Output short-circuit current (for negative output	I _{OS} (-)	$\pm V_{CC} = \pm 15 \text{ V}, \qquad \underline{3}/$ t $\leq 25 \text{ ms}, \text{ only one}$ amplifier shorted to GND at one time	1,2	01,02		55	mA
			3 <u>4</u> /	01,02		75	
				03,04		80	
Supply current	Icc	$\pm V_{CC} = \pm 15 \text{ V} \underline{5}/$	1,2	01,02		+3.6	mA
				03		+7	1
				04		+11	
		+V _{CC} = 30 V <u>5</u> /		05,06		+3	
		±V _{CC} = ±15 V <u>5</u> /	3	01,02		+4.5	
				03		9	
				04		+13	-
		V _{CC} = 30 V <u>5</u> /	•	05,06		+4	
Output voltage swing (maximum)	+V _{OP}	$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{L} = 10 \text{ k}\Omega$	4,5,6	01,02, 03,04	+16		V
		V_{CC} = 30 V, R _L = 10 k Ω		05,06	+27		
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{L} = 2 \text{ k}\Omega$	-	01,02, 03,04	+15		-
		V_{CC} = 30 V, R _L = 2 k Ω		05,06	+26		
	-V _{OP}	$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{\text{L}} = 10 \text{ k}\Omega$		01,02, 03,04		-16	
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{\text{L}} = 2 \text{ k}\Omega$		01,02, 03,04		-15	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test		Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Limits		Unit
			unless otherwise specified			Min	Max	
Single ended open	<u>6</u> /	A _{VS} (+)	$\pm V_{O} = \pm 15 V,$	4	01,02, 03,04	50		V/mV
loop voltage gain			R _L = 10 kΩ					_
			$V_{O} = 1 V \text{ to } 26 V,$		05,06	50		
			R _L = 10 kΩ					
			$\pm V_{O} = \pm 15 V,$	5,6	01,02, 03,04	25		
			RL = 10 kΩ		03,04			
			$V_{O} = 1 V \text{ to } 26 V,$		05,06	25		
			$R_L = 10 \text{ k}\Omega$					
		Avs(-)	$\pm V_{O} = \pm 15 \text{ V},$	4	01,02,	50		
			$R_L = 2 k\Omega$		03,04			
			$V_{O} = 5 V \text{ to } 20 V,$		05,06	50		
			$R_L = 2 k\Omega$					
			$\pm V_{O} = \pm 15 V,$	5,6	01,02,	25		
			$R_L = 2 k\Omega$		03,04			
			$V_{O} = 5 V \text{ to } 20 V,$		05,06	25		
			$R_L = 2 k\Omega$					
		Avs	$\pm V_{CC} = \pm 5 \text{ V}, \text{ V}_{O} = \pm 2 \text{ V},$	4	01,02,	10		
			R_L = 10 k Ω and 2 k Ω		03,04			
			V _{CC} = 5 V,		05,06	10		
			$V_{O} = 1 V \text{ to } 2.5 V,$					
			R_L = 10 k Ω and 2 k Ω					
			$\pm V_{CC} = \pm 5 \text{ V}, \text{ V}_{O} = \pm 2 \text{ V},$	5,6	01,02,	10		
		R_L = 10 k Ω and 2 k Ω		03,04				
			V _{CC} = 5 V,		05,06	10		
			$V_{O} = 1 V \text{ to } 2.5 V,$					
			R_L = 10 k Ω and 2 k Ω					

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Limits		Unit
		unless otherwise specified			Min	Max	
Low level output voltage	V _{OL}	+V _{CC} = 30 V, R _L = 10 k Ω	4,5,6	05,06		35	mV
		+V _{CC} = 30 V, I _{OL} = 5 mA				1.5	V
		+V _{CC} = 4.5 V, I _{OL} = 2 μA				0.4	
High level output voltage	V _{OH}	+V _{CC} = 30 V, I _{OH} = 10 mA	4,5,6	05,06	27		V
		+V _{CC} = 4.5 V, I _{OH} = 10 mA	4,5		2.4		
			6		2.3		
Transient response rise time	TR _(tr)	$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 1 \frac{7}{2}$ see figure 4	7,8A,8B	01,02		1.0	μs
				03		0.2	
				04		0.3	
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 5 \frac{7}{2}$ see figure 4		01,02		1.0	
		+V _{CC} = 30 V, A _V = 1 $\underline{7}$ / see figure 4		05,06		1.0	
Transient response overshoot	TR _(OS)	$\pm V_{CC} = \pm 20 \text{ V}, \underline{7}/$ see figure 4	7,8A,8B	01,02		25	%
				03		35]
				04		50	1
		$+V_{CC} = 30 \text{ V}, \frac{7}{2}$ see figure 4		05,06		60	1

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C \leq T _A \leq +125°C see figure 2	Group A subgroups	Device type	Limits		Unit
		unless otherwise specified			Min	Max	
Slew rate <u>9</u> /	SR(+) and	$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 1,$ see figure 5	7,8A,8B	01	+0.2		V/µs
	SR(-)			03	0.8		
				04	0.6		
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 5,$ see figure 5		02	0.8		
		$V_{CC} = 30 V, A_V = 1,$ see figure 5		05,06	0.1		
Noise (broadband)	NI(BB)	$\pm V_{CC}$ = ± 20 V, R _S = 50 Ω ,	9	01,02		15	μV rms
		T _A = +25°C		03,04		5	
		\pm V _{CC} = ±15 V, R _S = 50 Ω, T _A = +25°C		05,06		15	
Noise (popcorn)	NI(PC)	$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{\text{S}} = 20 \text{ k}\Omega,$	9	01,02		40	μV peak
		T _A = +25°C		03,04		50	1
		$\pm V_{CC} = \pm 15 \text{ V}, \text{ R}_{S} = 20 \text{ k}\Omega,$ T _A = +25°C		05,06		50	1

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $-55^{\circ}C \le T_A \le +125^{\circ}C$ see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Channel separation	CS	T _A = +25°C, see figure 7	7	01,02, 03,04, 05,06, 07,08	80		dB

TABLE I. Electrical performance characteristics - Continued.

<u>1</u>/ Device types 01 to 04 shall be tested at $V_{CM} = 0 \text{ V}$, +15 V, and -15 V with $\pm V_{CC} = \pm 20 \text{ V}$; and at $V_{CM} = 0 \text{ V}$ with $\pm V_{CC} = \pm 5 \text{ V}$. Device types 05 and 06 should be tested at $V_{CM} = -13 \text{ V}$ with $V_{CC} = 2 \text{ V}$ and $-V_{CC} = -28 \text{ V}$; $V_{CM} = +15 \text{ V}$ with $+V_{CC} = 30 \text{ V}$ and $-V_{CC} = 0 \text{ V}$; $V_{CM} = +1.4 \text{ V}$ with $V_{CC} = 5 \text{ V}$ and $-V_{CC} = 0 \text{ V}$; $V_{CM} = -1.1 \text{ V}$ at $\pm V_{CC} = 2.5 \text{ V}$.

2/ CMR is determined by measuring input offset voltage as follows:

Offset voltage			Device	e types			Units
condition		01 - 04		(05 and 06	6	
	+Vcc	-Vcc	Vo	+V _{CC}	-Vcc	Vo	
1	35	-5	15	30	0	15	V
2	5	-35	-15	2	-28	-13	V

3/ Continuous limits will be considerably lower and apply for $-55^{\circ}C \le T_A \le 25^{\circ}C$.

- $\frac{4}{I_{SO(+)}}$ and $I_{SO(-)}$ limits for device type 01 only at $T_A = -55^{\circ}C$ are -75 mA and 75 mA respectively.
- 5/1 LCC limits are the total for all four amplifiers at no load, connected as grounded followers.
- 6/ AVS(+) for device types 05 and 06 only.
- <u>7</u>/ Device types 05 and 06 transient response is specified with the input pulse referenced to 5 V. For application purposes the device may be operated with the input referenced to ground, however, saturation effects will cause the response time to increase by approximately 50 percent.

TABLE II.	Electrical test requirements.	

MIL-PRF-38535 test requirements	Subgroups	(see table III)
	Class S devices	Class B devices
Interim electrical parameters	1	1
Final electrical test parameters <u>1</u> /	1,2,3,4	1,2,3,4
Group A test requirements	1,2,3,4,5,6, 7,8	1,2,3,4,5,6, 7,8
Group B electrical test parameters when using the method 5005 QCI option	1,2,3,4,5,6, 7,8	N/A
Group C end point electrical parameters	1,2,3, and table IV delta limits	1 and table IV delta limits
Group D end point electrical parameters	1,2,3	1

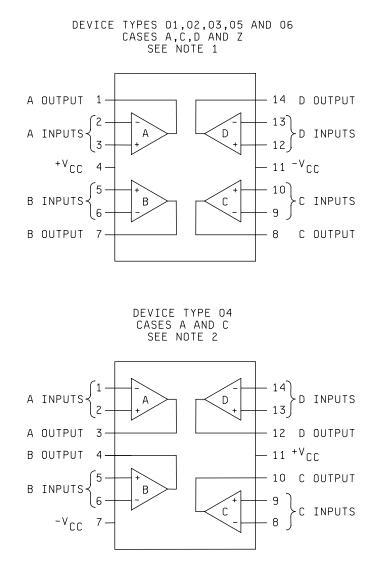
<u>1</u>/ PDA applies to subgroup 1.

4. VERIFICATION.

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as function as described herein.

4.2 <u>Screening</u>. Screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535.
- 4.3 <u>Qualification inspection</u>. Qualification inspection shall be in accordance with MIL-PRF-38535.



NOTES:

- 1. 14 lead flat pack, dual in line package, and gullwing flat pack.
- 2. 14 lead flat pack and dual in line package.

FIGURE 1. Case outlines and terminal connections.

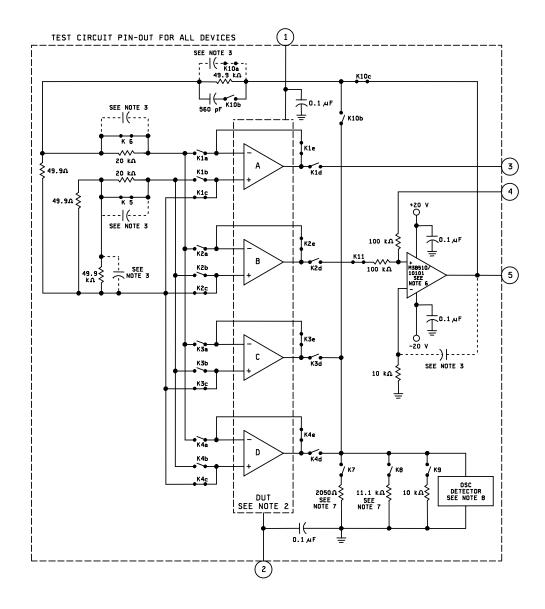


FIGURE 2. Test circuit for static tests.

NOTES:

- <u>1</u>/ All resistors ± 0.1 percent tolerance and all capacitors are ± 10 % tolerance.
- 2/ Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state of relays (i.e. disable voltage supplies, current limit ±V_{CC}, etc.).
- 3/ Stabilizing capacitors may be added as required, if needed to prevent oscillations. Also, proper wiring procedures shall be followed to prevent oscillations. Loop response and settling time shall be consistent with the test rate such that any value has settled for at least five loop time constants before the value is measured, however, adequate settling time shall be allowed such that each parameter has settled to within five percent of its final value. There are two general methods to stabilize the test circuit: One method is with a capacitor in the nulling amplifier feedback loop and the other method is with a capacitor in parallel with the 49.9 kΩ closed loop feedback resistor. Both methods shall not be used simultaneously.
- 4/ All relays are shown in the normal de-energized state. Relays K1, K2, K3, and K4 select amplifiers A, B, C, and D respectively. The rest of the relays are used to select the conditions for each test.
- 5/ Each amplifier shall be tested separately, except for the ICC measurements where all the amplifiers shall be connected as grounded followers (relays K1 through K4 de-energized).
- 6/ The nulling amplifier should be an M38510/11001XXXor similar. Saturation of the nulling amplifier is not allowed on test where the E (pin 5) value is measured.
- <u>I</u>/ The load resistors 2,050 Ω and 11.1 k Ω yield effective load resistances of 2 k Ω and 10 k Ω , respectively.
- 8/ Any oscillation greater that 300 mV in amplitude (peak peak) shall be a cause for device failure.

FIGURE 2. <u>Test circuit for static tests</u>- Continued.

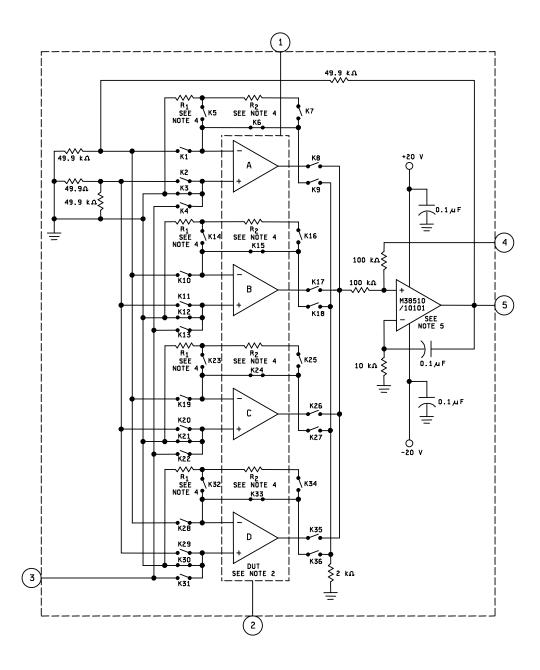


FIGURE 3. Test circuit for channel separation.

Test requirements.

CS test number*	Channels tested		Relays ene	ergized
		All c	levice types	Additional for device type 02
		Driven	Monitored	Driven
103 (100)	A to B	3,4,9	10,11,12,15,17	5,6,7
104 (101)	A to C	"	19,20,21,24,26	"
105 (102)	A to D	"	28,29,30,33.35	"
106 (103)	B to A	12,13,18	1,2,3,6,8	14,15,16
107 (104)	B to C	"	19,20,21,24,26	"
108 (105)	B to D	"	28,29,30,33,35	"
109 (106)	C to A	21,22,27	1,2,3,6,8	23,24,25
110 (107)	C to B	"	10,11,12,15,17	"
111 (108)	C to D	"	28,29,30,33,35	"
112 (109)	D to A	30,31,36	1,2,3,6,8	32,33,34
113 (110)	D to B	"	10,11,12,15,17	"
114 (111)	D to C	"	19,20,21,24,26	"

* Numbers in parenthesis apply to device types 05 and 06.

- 2/ Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state relays (i.e. disable voltage supplies, current limit ±V_{CC}, etc.).
- 3/ All relays are shown in the normal de-energized state. The above table shall be used to determine which relays to energize for each test.
- $\underline{4}$ R₁ and R₂ shall be used with device type 02 only and shall be such that A_V = 5 V/V.
- 5/ The nulling amplifier shall be a M38510/11001XXX or similar. Saturation of the nulling amplifier is not allowed.

FIGURE 3. Test circuit for channel separation - Continued.

<u>1</u>/ All resistors are ± 0.1 % tolerance and all capacitors are $\pm 10\%$.

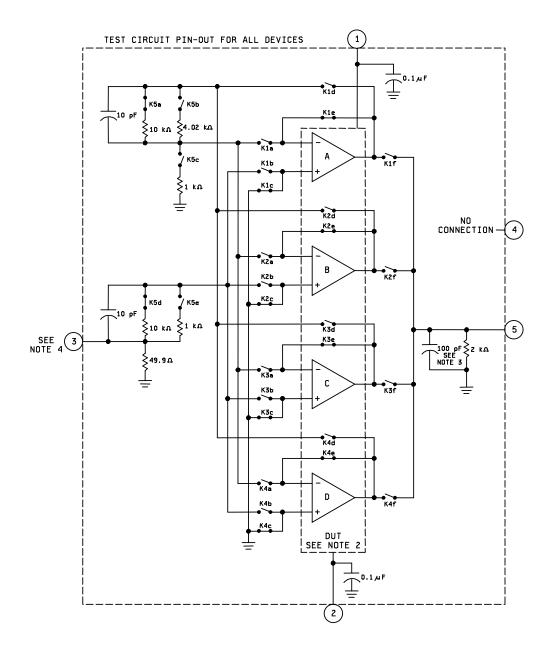
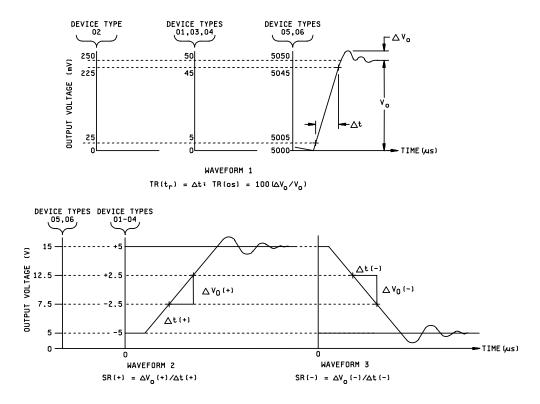


FIGURE 4. Test circuit and waveform for transient response .



- <u>1</u>/ All resistors are ± 0.1 % tolerance and all capacitors are $\pm 10\%$ tolerance.
- 2/ Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state of relays (i.e. disable voltage supplies, current limit ±V_{CC}, etc.).
- 3/ This capacitance includes the actual measured value with stray and wire capacitance.
- 4/ Relays K1, K2, K3, and K4 select amplifiers A, B, C, and D respectively. Relay K5 shall be energized for device type 02 only. The input pulse shall have the following characteristics:

FIGURE 4. Test circuit and waveform for transient response - Continued.

Input pulse table

Parameter symbol	Device type	Rise time	Amplitude
TR(t _r)	01,03,04	50 ns or less	+50 mV referenced to GND
	02		+250 mV referenced to GND
	05,06		+50 mV referenced to 5 V
TR(os)	01,03,04		+50 mV referenced to GND
	02		+250 mV referenced to GND
	05,06		+50 mV referenced to 5 V
SR(+)	01,03,04		-5 V to +5 V step
	02		-1 V to +1 V step
	05,06		+5 V to +15 V step
SR(-)	01,03,04		+5 V to -5 V step
	02		+1 V to -1 V step
	05,06		+15 V to +5 V step

FIGURE 4. Test circuit and waveform for transient response - Continued.

	jit			>				4				Ŧ				4				2	2	m	٨			>			
	Unit			∧ ¤	3	3	3	ЧЧ	3	3	3	ΡU	*	3	3	PA	3	3	3	N/Λμ	μV/V	В	шA	3	77	> E	3	3	3
	04	Limits	Max	£±	£¦	72	£∃	±75	±75	±75	±75	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100	±100			80	11	9 ∓	9 <u>∓</u>	9 <u>∓</u>	9 ∓
			Min									-250	-250	-250	-250	-250	-250	-250	-250			76	-80						
types	8	its	Max	13	∓3	∓3	∓3	±30	±30	±30	±30	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100	±100			80	7	72	72	72	72
Device types	03	Limits	Min									-200	-200	-200	-200	-200	-200	-200	-200			76	-80						
	0	~	Мах	72	1 5	72	12	±25	±25	±25	±25	100	100	100	100	100	100	100	100	±100	±100			55	3.6	9∓	9	9	9∓
	01, 02	Limits	Min									-0.1	-0.1	-0.1	-0.1	-0.1	-0.1	-0.1	-0.1			76	-55						
			~									'					1	1	1	×	×								
		Equations $\frac{3}{}$		VIO = E1	VIO = E2	VIO = E3	VIO = E4	IIO = 50 (E1 – E5)	IIO = 50 (E2 – E6)	IIO = 50 (E3 – E7)	IIO = 50 (E4 – E8)	+IIB = 50 (E1 –E9)	+IIB = 50 (E2 –E10)	+IIB = 50 (E3 –E11)	+IIB = 50 (E4 –E12)	-IIB = 50 (E13 –E1)	-IIB = 50 (E14 –E2)	-IIB = 50 (E15 –E3)	-IIB = 50 (E16 –E4)	+PSRR = (E3 – E17) 100	-PSRR = (E3 – E18) x 100	CMR = 20 log 3 × 10 ⁴ / E1 – E2	lOS(+) = l1	IOS(-) = I2	ICC = 13	VIO = E19	VIO = E20	VIO = E21	VIO = E22
		ns	Unit	^	2	ä	a	a	a	3	3	ä	a	2	2	2	3	2	3	3	ĸ		mA	ä	n	>	3	3	я
		Measured pins	Value	E1	E2	E3	E4	E5	E6	Ε7	E8	Еg	E10	E11	E12	E13	E14	E15	E16	E17	E18		7	12	l3	E19	E20	E21	E22
		Me	No.	5																I			ю	3	2	5	5	5	5
	Energized	relays <u>2</u> /		None	z	2	z	K5, K6	3	z	z	K5	*	z	z	K5	z	z	z	None	None		None	3	n	z	2	2	z
	ш	_	5																			and 2							
	ers		4	-15 V	15 V	GND	GND	-15 V	15 V	GND	GND	-15 V	15 V	GND	GND	-15 V	15 V	GND	GND	GND	GND	m tests 1	-10 V	10 V		-15 V	15	GND	GND
	dmun nia		ю	-												-						g data fro	GND	GND		-			
	Adapter pin numbers		2	-5 V	-35 V	-20 V	-5 V	-5 V	-35 V	-20 V	-5 V	-5 V	-35 V	-20 V	-5 V	-5 V	-35 V	-20 V	-5 V	-20 V	-10 V	alue usinç	-15 V	-15 V	-15 V	-5 V	-35 V	-20 V	-5 V
			+	35 V	5 V	20 V	5 V	35 V	5 V	20 V	5 V	35 V	5 V -	20 V	5 V	35 V	5 V	20 V	5 V	10 V	20 V	Calculate value using data from tests 1 and 2	15 V -	15 V -	15 V -	35 V	5 V	20 V	5 V
	est			<u>4</u> / 3	<u>4</u> /	2/	<u>4</u> / 5	5 3	6 5		8	9 3	10 5	11 2	12 5	13 3	14 5	15 2	16 5	17 1	18 2	4/	<u>6</u> /	<u>6</u> /	7/	4/	4/	<u>4/ 5/</u> 2	4/
	D Test	.ou	77	-	2	3 4/	4	U)	Φ	7	ω	0,	-	-	-	-	4	-	-	,	-	19	20	21	22	23	24	25 4	26
	MIL-STI	-883	method	4001	3	2	2	2	2	3	2	2	2	2	3	3	3	3	*	4003	4003	4003	3011	3011	3005	4001	3	3	a
	Symbol MIL-STD			VIO				일				8 + +				-IB				+PSRR	-PSRR	CMR	los(+)	los(-)	Icc	VIO			
	Subgroup			٢	TA =	+25°C																				7	TA =	+125°C	

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

	04 Unit	Limits	Max	±25 μ//°C		±75 nA	±75 "		±75 "	±500 pA/°C	+0.1 nA	+0.1 "	+0.1	+0.1 "	+0.1 nA	+0.1 "	+0.1	+0.1 "	±100 μV/V	±100 μV/V	dВ	mA	80 "	11 "	±6 mV	" +6	" ∓9	" ∓9
			Min								-250	-250	-250	-250	-250	-250	-250	-250			76	-80						
Device types	03	Limits	Max	±20		±30	±30	130	±30	±200	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100	±100			80	7	1 €	1 2	1 2	£±
Devi			Min								-200	-200	-200	-200	-200	-200	-200	-200			76	-80						
	01, 02	Limits	Мах	±25		±25	±25	±25	±25	±200	100	100	100	100	100	100	100	100	±100	±100			55	3.6	9 ∓	9∓	9 ∓	9 ∓
	Ō		Min								-0.1	-0.1	-0.1	-0.1	-0.1	-0.1	-0.1	-0.1			76	-55						
		Equations $\underline{3}$				IIO = 50 (E19 – E23)	lIO = 50 (E20 – E24)	lIO = 50 (E21 – E25)	lIO = 50 (E22 – E26)		+IIB = 50 (E19 -E27)	+IIB = 50 (E20 –E28)	+IIB = 50 (E21 –E29)	+IIB = 50 (E22 –E30)	-IIB = 50 (E31 –E19)	-IIB = 50 (E32 -E20)	-IIB = 50 (E33 -E21)	-IIB = 50 (E34 -E22)	+PSRR = (E21 – E35) x 100	-PSRR = (E21 – E36) x 100	CMR = 20 log 3 x 10 ⁴ / E19 – E20	lOS(+) = l4	10S(-) = 15	ICC = 16	VIO = E37	VIO = E38	VIO = E39	VIO = E40
		ins	Unit			>	a	z	и		>	z	¥	z	¥	z	z	z	z	ч		шA	z	z	>	z	2	и
		Measured pins	Value			E23	E24	E25	E26		E27	E28	E29	E30	E31	E32	E33	E34	E35	E36		14	I5	le	E37	E38	E39	E40
			No.			5	a	z	u		5	3	3	*	¥	×	z	2	2	2		3	3	2	5	5	5	5
	Energized	relays <u>2</u> /		/ 100°C		K5, K6	3	2	10	100°C	K5	a	3	31	K6	31	3	7	None	None	24.	None			None			
			5	(Test 3)),						(Test 7)) /											s 23 and ;							
	nbers		4	= (VIO (Test 25 - VIO (Test 3)) / 100°C		-15 V	15 V	GND	GND	= (IIO (Test 30) – IIO (Test 7)) / 100°C	-15 V	15 V	GND	GND	-15 V	15 V	GND	GND	GND	GND	Calculate value using data from tests 23 and 24.	-10 V	10 V		-15 V	15	GND	GND
	Adapter pin numbers		3	/IO (Test						IIO (Test:											ising data	GND	GND					
	Adapt		2	ΔVIO / ΔT = (^v		-5 V	-35 V	-20 V	-5 V	ΔVIO / ΔT = (-5 V	-35 V	-20 V	-5 V	-5 V	-35 V	-20 V	-5 V	-20 V	-10 V	te value u	-15 V	-15 V	-15 V	-2	-35 V	-20 V	-5 V
			٢	ΝVΔ		35 V	5 V	20 V	5 V	ΔVI	35 V	5 V	20 V	5 V	35 V	5 V	20 V	5 V	10 V	20 V	Calcula	15 V	15 V	15 V	35 V	5 V	20 V	5 <
	Test	no.		27		28	29	30	31	32 <u>8</u> /	33	34	35	36	37	38	39	40	41	42	43 <u>4</u> /	44 <u>6</u> /	45 <u>6</u> /	46 <u>7</u> /	47 4/	48 <u>4</u> /	49 <u>4</u> /	50 4/
	MIL-STD	-883	method	4001	3	3	39	3	79	33	3	з	3	3	3	33	з	н	4003	4003	4003	3011	3011	3005	4001			
	Symbol MIL-STD			/ OIVΔ	ΔT	ol				ΔΙΙΟ/ΔΤ	+IB				-IIB				+PSRR	-PSRR	CMR	lOS(+)	los(-)	20	OIN			
	Subgroup			2	TA =+125°C																				7	TA =	-55°C	

24

TABLE III.	Group A inspection for device types 01, 02, 03, and 04.	1/
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Energized
Adapter pri numbers Energy 20
4 5
= (VIO (Test 3 – VIO (Test 49)) / 80°C
-15 V K5, K6
= (IIO (Test 7 – IIO (Test 54)) / 80°C
K5
K6
None
None
Calculate value using data from tests 47 and 48
None
K8
20 V K8
-20 V K7

25

	Unit			V/m/	3	3	3	*	*	3	n	>	3	3	*	/m/	3	3	*	3	2	3	3	>	*	3	*
	04	Limits	Мах										-16		-15										-16		-15
	0	Lir	Min	50	50	50	50	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
Device types	03	Limits	Max										-16		-15										-16		-15
Device	0	Lin	Min	50	50	50	50	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
	02	its	Max										-16		-15										-16		-15
	01, 02	Limits	Min	50	50	50	50	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
		Equations <u>3</u> /		AVS(+) = 15/(E3 – E55)	AVS(+) = 15/(E3 – E56)	AVS(-) = 15/(E57 – E3)	AVS(-) = 15/(E58 – E3)	AVS = 4/(E60 - E59)		AVS = 4/(E62 – E61)		+VOP = (E0)5	-VOP = (E0)6	+VOP = (E0)7	-VOP = (E0)8	AVS(+) = 15/(E21 – E63)	AVS(+) = 15/(E21 - E64)	AVS(-) = 15/(E65 – E21)	AVS(-) = 15/(E66 - E21)	AVS = 4/(E68 – E67)		AVS = 4/(E70 – E69)		+VOP = (E0)9	-VOP = (E0)10	+VOP = (E0)11	-VOP = (E0)12
		ns	Unit	^	*	ä	ä	ÿ	¥	ų	ų	ä	n	*	¥	*	*	"	3	3	3	3	n	*	¥	ų	ú
		Measured pins	Value	E55	E56	E57	E58	E59	E60	E61	E62	(E0)5	(E0)6	(E0)7	(E0)8	E63	E64	E65	E66	E67	E68	E69	E70	(E0)9	(E0)10	(E0)11	(E0)12
		Me	No.	5	3	*	*	*	3	3	**	3	3	ю	3	5	3	3	2	3	3	3	ч	3	ю	ю	3
	Energized	relays <u>2</u> /		K8	K7	K8	K7	K8	K8	K7	K7	K8	K8	K7	K7	K8	K7	K8	K7	K8	K8	K7	K7	K8	K8	K7	K7
	ш	-	5																								
	oers		4	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 V	-20 V	20 V	-20 V	20 V	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 V	-20 V	20 V	-20 V	-20 V
	Adapter pin numbers		3																								
	Adapter		2	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 V	-20 V	-20 V	-20 V	-20 V
			-	20 V	20 V	20 V	20 V	5 V	5 V	5 V	5 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	5 V	5 V	5 V	5 V	20 V	20 V	20 V	20 V
	Test	Ou	L	75 <u>5</u> /	76 <u>5</u> /	77 <u>5</u> /	78 <u>5</u> /	79		80		81	82	83	84	85 <u>5</u> /	86 <u>5</u> /	87 <u>5</u> /	88 <u>5</u> /	89		06		91	92	93	94
	111-STD	-883	method	4004	2	3	3	z	3	z	3	3	z	z	2	2	z	z	z	39	3	z	3	z	3	z	u
	Symbol MIL-STD		L	AVS(+)	AVS(+)	AVS(-)	AVS(-)	AVS				+VOP	-VOP	+VOP	-VOP	AVS(+)	AVS(+)	AVS(-)	AVS(-)	AVS				+VOP	-VOP	+VOP	-VOP
	Subgroup			4	TA =+25°C							5	TA =+125°C							<u> </u>				9	TA =	-55°C	

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

	Unit			V/m/V	3	39	3	3	**	a	39	μVrms	цVpk	đB	79	33	39	79	3	3	31	3	39	39	39	59	3	39	з	39	3
	04	Limits	Max									5	50																		
	0	Lin	Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
Device types	03	Limits	Max									5	50																		
Device	0	Lin	Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
	01, 02	Limits	Max									15	40																		
	01	Lir	Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
		Equations <u>3</u> /		AVS(+) = 15/(E39 – E71)	AVS(+) = 15/(E39 – E72)	AVS(-) = 15/(E73 – E39)	AVS(-) = 15/(E74 – E39)	AVS = 4/(E76 - E75)		AVS = 4/(E78 – E77)		NI(BB) = (E0)13	NI(PC) = (E0)14	CS = 20 log	2 × 10 ⁴ / E79 – E80	CS = 20 log	2 × 10 ⁴ / E81 – E82	CS = 20 log	2 x 10 ⁴ / E83 – E84	CS = 20 log	2 x 10 ⁴ / E85 – E86	CS = 20 log	2 × 10 ⁴ / E87 – E88	CS = 20 log	2 × 10 ⁴ / E89 – E90	CS = 20 log	2 × 10 ⁴ / E91 – E92	CS = 20 log	2 × 10 ⁴ / E93 – E94	CS = 20 log	2 x 10 ⁴ / E95 – E96
		su	Unit	>	z	3	z	a	a	ä	z	mVrms	mVpk	>	з	z	3	ч	3	2	3	z	a	a	ч	ч	z	z	2	z	3
		Measured pins	Value	E71	E72	E73	E74	E75	E76	E77	E78	(E0)13	(E0)14	E79	E80	E81	E82	E83	E84	E85	E86	E87	E88	E89	E90	E91	E92	E93	E94	E95	E96
		Me	No.	5	3	**	3	79	*	n	77	3	ю	5	79	**	**	79	з	39	33	39	n	33	77	39	3	33	3	33	з
	Energized	relays <u>2</u> /		K8	K7	K8	K7	K8	K8	K7	K7	K10, K11	K5, K6, K10, K11	See fig. 3	a	a	a	a	2	3	3	3	ä	z	a	a	z	z	z	¥	z
			5																												
	hers		4	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 V	GND	3	я	u	39	n	11	37	75	99	89	99	10	11	10	a	3	з	16	**
	Adapter pin numbers		3											<u>11</u> /	<u>12/</u>	<u>11</u> /	<u>12/</u>	<u>11</u> /	12/	<u>11</u> /	<u>12</u> /	<u>11</u> /	<u>12/</u>	<u>11</u> /	<u>12</u> /						
	Adapte		2	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V
			1	20 V	20 V	20 V	20 V	5 V	5 V	5 V	5 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V
	Test	.ou		95	96	97	86	66		100 <u>9</u> /		101 <u>10</u> /	102	103		104		105		106		107		108		109		110		111	
	MIL-STD	-883	method	4004	z	3	3	3	3	z	2									1											
	Symbol			AVS(+)	AVS(+)	AVS(-)	AVS(-)	AVS				NI(BB)	NI(PC)	cs																	
	Subgroup			9	TA =-55°C							7	TA =+25°C	I																	

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

= 111	. <u>G</u>	100	р <i>Р</i>	1110	pec				<u>,, , , , , , , , , , , , , , , , , , ,</u>	pes	01, 02	2, 03, 7		<u>4</u> . <u>1</u> /
	Unit			đB	3	3	"	"	n	SH	%	V/µs	V/µs	
	+	its	Max							0.3	50			
	04	Limits	Min	80	80	80	80	80	80			0.6	0.6	
ypes		s	Max							0.2	35			
Device types	03	Limits	Min	80	80	80	80	80	80			0.8	0.8	
	~		Max							1.0	25			
	01, 02	Limits	Min	80	80	80	80	80	80			/ 6	<u>6</u>	
		Equations <u>3</u> /		CS = 20 log	2 × 10 ⁴ / E97 – E98	CS = 20 log	2 × 10 ⁴ / E99 – E100	CS = 20 log	2 x 10 ⁴ / E101 – E102	(Waveform 1) TR(t_r) = Δt	(Waveform 1) TR(OS) - 100 (ΔVO/VO)	(Waveform 2) SR(+) = VO/∆t	(Waveform 3) SR(-) = ∆VO/∆t	Same tests, terminal conditions and limits as subgroup7, tests 115 through 118 except $TA = 125^{\circ}C$ and $TA = -55^{\circ}C$.
			Unit	>	z	3	3	*	n	sni	>	V; µs	V; µs	cept TA =
		Measured pins	Value	E97	E98	E99	E100	E101	E102	Δt	νο;Δνο	ΔVO; Δt	ΔVO; Δt	rough 118 ex
		2	No.	5	3	**	55	55	3	3	2	3	3	ts 115 th
	Energized	relays <u>2</u> /		See fig. 3	z	z	3	3	и	See fig. 4	3	z	z	bgroup7, tes
			5							OUT				nits as su
	bers		4	GND	10	10	55	55	*	"	и	×	'n	ons and lir
	Adapter pin numbers		3	11/	12/	<u>11</u> /	12/	<u>11</u> /	12/	Z				al conditio
	Adapte		2	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	ts, termina
			٢	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	Same tes
	Test	ou		112		113		114		115	116	117	118	119 to 1 126
	MIL-STD	-883	method					<u> </u>			. <u></u>			
	Symbol M		L	cs						TR(tr)	TR(os)	SR(+)	SR(-)	
	Subgroup			7	TA =+25°C									8

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

				1							1						-71-			<u>u uo</u> .	<u> </u>							
	Unit			∧ m	2	3	3	ЧЧ	3	3	2	ЧЧ	2	2	3	ЧЧ	3	2	*	Ν/Λμ	39	dB	МА	шA	۲ ۲	3	3	3
	90	Limits	Max	77	±2	±2	1 2	±10	±10	±10	±10	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100				3	±4	±4	±4	44
types	0	Lim	Min									-50	-50	-50	-50	-50	-50	-50	-50			76	-70					
Device types		ts	Мах	72	7	72	72	±30	130	±30	±30	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100				3	±7	±7	±7	17
	05	Limits	Min									-150	-150	-150	-150	-150	-150	-150	-150			76	-70					
		Equations <u>3</u> /		VIO = E1	VIO = E2	VIO = E3	VIO = E4	lIO = 10 ⁶ (E1 – E5)/RS	lIO = 10 ⁶ (E2 – E6) /RS	lIO = 10 ⁶ (E3 – E7) /RS	lIO = 10 ⁶ (E4 – E8) /RS	+IIB = 10 ⁶ (E1 –E9) /RS	+IIB = 10 ⁶ (E2 –E10) /RS	+IIB = 10 ⁶ (E3 –E11) /RS	+IIB = 10 ⁶ (E4 -E12) /RS	-IIB = 10 ⁶ (E13 –E1) /RS	-IIB = 10 ⁶ (E14 –E2) /RS	-IIB = 10 ⁶ (E15 –E3) /RS	-IIB = 10 ⁶ (E16 –E4) /RS	+PSRR = (E17 – E18)	x 40	CMR = 20 log 2.8 x 10 ⁴ / E1 – E2	1) = I	ICC = 12	VIO = E19	VIO = E20	VIO = E21	VIO = E22
		ins	Unit	>	a	a	a	×	3	a	3	×	a	a	a.	3	33	a	*	2	3		mA	mA	>	*	7	*
		Measured pins	Value	E1	E2	E3	E4	E5	E6	ΕŢ	E8	Еg	E10	E11	E12	E13	E14	E15	E16	E17	E18		11	12	E19	E20	E21	E22
		Me	No.	5	2	3	3	×	2	×	3	×	×	2	*	3	3	3	*	33	3		3	2	5	3	3	3
	Energized	relays <u>2</u> /		None	3	79	10	K5, K6	3	3	11	K5	3	3	1	K6	57	4	11	None	None	12	None	None	None	ų	11	16
			5																			ts 1 and						
	bers		4	-15 V	13 V	-1.4 V	1.1 V	-15 V	13 V	-1.4 V	1.1 V	-15 V	13 V	-1.4 V	1.1 V	-15 V	13 V	-1.4 V	1.1 V	-1.4 V	-1.4 V	from test	-25 V		-15 V	13 V	-1.4 V	1.1 V
	oin num		ю																			ing date	GND					
	Adapter pin numbers		2	GND	-28 V	GND	-2.5 V	GND	-28 V	GND	-2.5 V	GND	-28 V	GND	-2.5 V	GND	-28 V	GND	-2.5 V	GND	GND	Calculate value using data from tests 1 and 2	GND	GND	GND	-28 V	GND	-2.5 V
			-	30 V	2 V	5 V	2.5 V	30 V	2 <	5 V	2.5 V	30 V	2 V	5 V	2.5 V	30 V	2 <	5 V	2.5V	30 V	5 V	Calculat	30 V	30 V	30 V	2 <	5 V	2.5 V
	Test	no.		1 4/	2 4/	3 4/	4 4/	5	9	7	8	9	10	11	12	13	14	15	16	17		18 <u>4</u> /	19 <u>6</u> /	20 <u>7</u> /	21 <u>4</u> /	22 4/	23 4/	24 <u>4</u> /
	MIL-STD	-883	method	4001			I									I	1			4003		4003	3011	3005	4001	2	z	з
	Symbol			VIO				<u>0</u>				+lB				-IB				+PSRR		CMR	lOS(+)	20	٥١			
	Subgroup			٦	TA =	+25°C																					3	TA =+125°C

TABLE III. Group A inspection for device types 05 and 06. 1/

	jŗ			ပ္စ	đ				õ	ď		3		∢				2		ш	A	A	>	3			ပ္စ
	Unit			μV/°C	hA	*	3	3	pA/°C	hA	3	2	**	hA	3	3	3	N/Λμ	3	dB	шA	шA	کم ۲	3	3	"	μ\/'°C
	06	Limits	Max	±30	±10	±10	±10	±10	±400	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100				3	44	±4	±4	±4	±30
Device types	0	Li	Min							-50	-50	-50	-50	-50	-50	-50	-50			76	-70						
Device		ts	Мах	±30	±30	±30	±30	±30	±400	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100				3	±Ζ	±7	±7	± 7	±30
	05	Limits	Min							-150	-150	-150	-150	-150	-150	-150	-150			76	-70						
		Equations <u>3</u> /			IIO = 10 ⁶ (E19 – E23)/RS	lIO = 10 ⁶ (E20 – E24)/ RS	lIO = 10 ⁶ (E21 – E25)/ RS	lıO = 10 ⁶ (E22 – E26)/ RS		+IIB = 10 ⁶ (E19 –E27)/ RS	+IIB = 10 ⁶ (E20 –E28)/ RS	+IIB = 10 ⁶ (E21 –E29)/ RS	+IIB = 10 ⁶ (E22 –E30)/ RS	-llB = 10 ⁶ (E31 –E19)/ RS	-lIB = 10 ⁶ (E32 –E20)/ RS	-IIB = 10 ⁶ (E33 –E21)/ RS	-IIB = 10 ⁶ (E34 –E22)/ RS	+PSRR = (E35 – E36)	x 40	CMR = 20 log 2.8 x 10 ⁴ / E19 – E20	lOS(+) = l3	ICC = 14	VIO = E37	VIO = E38	VIO = E39	VIO = E40	
		ins	Unit		>	×	z	3		>	z	×	z	2	2	2	z	3	3		mA	mA	>	2	2	ä	
		Measured pins	Value		E23	E24	E25	E26		E27	E28	E29	E30	E31	E32	E33	E34	E35	E36		l3	14	E37	E38	E39	E40	
		Me	No.		5	33	3	3		5	33	3	3	3	3	3	3	n	*		3	2	5	33	3	16	
	Energized	relays <u>2</u> /		/ 100°C	K5, K6	**	a	a	100°C	K5	3	3	10	K6	33	39	10	None	None	22.	None	None	None	59	31	16	/ 80°C
			5	Test 3)) .					est 7)) /											21 and							[est 45]
	bers		4	3 – VIO (-15 V	13 V	-1.4 V	1.1 V	3 – IIO (T	-15 V	13 V	-1.4 V	1.1 V	-15 V	13 V	-1.4 V	1.1 V	-1.4 V	-1.4 V	rom tests	-25 V		-15 V	13	-1.4 V	1.1 V	3 – VIO (⁻
	Adapter pin numbers		3	D (Test 2) (Test 28											ng data f	GND						O (Test 3
	Adapter		2	ΔVIO / ΔT = (VIO (Test 23 - VIO (Test 3)) / 100°C	GND	-28 V	GND	-2.5 V	∆l O / ∆T = (I O (Test 28 – I O (Test 7)) / 100°C	GND	-28 V	-GND	-2.5 V	GND	-28 V	GND	-2.5 V	GND	GND	Calculate value using data from tests 21 and 22.	GND	GND	GND	-28 V	GND	-2.5	ΔVIO / ΔT = (VIO (Test 3 – VIO (Test 45)) / 80°C
			1	۵VIO	30 V	2 V	5 V	2.5 V	OII∆	30 V	2 V	5 V	2.5 V	30 V	2 V	5 V	2.5 V	30 V	5 V	Calculate	30 V	30 V	30 V	2 V	5 V	2.5 V	ΔVIO
	Test	no.		25	26	27	28	29	30 <u>8</u> /	31	32	33	34	35	36	37	38	39		40 <u>4</u> /	41 <u>6</u> /	42 <u>7</u> /	43 4/	44 <u>4</u> /	45 <u>4</u> /	46 4/	47 <u>8</u> /
	MIL-STD	-883	method	4001	2	3	z	3	3	z	2	z	2	3	3	z	и	4003	3	4003	3011	3005	4001				
	Symbol			ΔVΙΟ / ΔΤ	0				∆lı0/∆T	₽ B				-IB				+PSRR		CMR	lOS(+)	lcc	ΟΙΛ				ΔVΙΟ / ΔΤ
	Subgroup			2	TA =+125°C																		2	TA =	+125°C		

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

	Unit			ЧЧ	3	3	*	pA/°C	ЧЧ	3	3	*	ΡU	3	3	3	μV/V	11	đB	mA	3	>	3	V/m/V	*	3	ä
	ر		XE		±30	0	30			1	E.	1		1	1	1		00	-	-				>			
	90	Limits	Max	∓30	θ H	±30	±30	±700	0 +0.1	0 +0.1	0 +0.1	0 +0.1	0 +0.1	0 +0.1	0 +0.1	0 +0.1	±100	±100			4						
Device types			Min						-100	-100	-100	-100	-100	-100	-100	-100			76	-70		27	26	50	50	50	50
Devi	05	Limits	Мах	±75	±75	±75	±75	±700	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	+0.1	±100	±100			4						
	0	Lin	Min						-300	-300	-300	-300	-300	-300	-300	-300			76	-70		27	26	50	50	50	50
		Equations <u>3</u> /		lIO = 10 ⁶ (E37 – E41)/RS	lIO = 10 ⁶ (E38 – E42) /RS	lIO = 10 ⁶ (E39 – E43) /RS	lIO = 10 ⁶ (E40 – E44) /RS		+IIB = 10 ⁶ (E37 –E45) /RS	+IIB = 10 ⁶ (E38 –E46) /RS	+IIB = 10 ⁶ (E39 –E47) /RS	+IIB = 10 ⁶ (E40 –E48) /RS	-IIB = 10 ⁶ (E49 –E37) /RS	-IIB = 10 ⁶ (E50 –E38) /RS	-lıB = 10 ⁶ (E51 –E39) /RS	-IIB = 10 ⁶ (E52 –E40) /RS	+PSRR = (E53 – E54) x 40		CMR = 20 log 2.8 x 10 ⁴ / E37 – E38	lOS(+) = 15	ICC = I6	+VOP = (E0)1	+VOP = (E0)2	AVS(+) = 25/(E56 – E55)		AVS(+) = 15/(E58 – E57)	
		ins	Unit	>	2	3	3		>	*	2	×	3	3	×	2	2	*		mA	mA	>	3	3	3	3	я
		Measured pins	Value	E41	E42	E43	E44		E45	E46	E47	E48	E49	E50	E51	E52	E53	E54		I5	le	(E0)1	(E0)2	E55	E56	E57	E58
		Ŵ	No.	5	3	и	×		5	×	3	3	ä	ä	z	3	z	ŕ		3	2	3	3	5	ä	×	'n
	Energized	relays <u>2</u> /		K5, K6	и	21	*	80°C	K5	×	3	16	K6	3	×	н	None	None	44.	None	None	K8	K7	K8	K8	K7	K7
			5					-est 7)) /											43 and								
	bers		4	-15 V	13 V	-1.4 V	1.1 V	0 – I O (]	-15 V	13 V	-1.4 V	1.1 V	-15 V	13 V	-1.4 V	1.1 V	-1.4 V	-1.4 V	rom tests	-25 V		-30 V	-30 V	-26 V	-1 <	-20 V	-5 V
	Adapter pin numbers		3					D (Test 5											ng data fi	GND							
	Adapter		2	GND	-28 V	GND	-2.5 V	∆IIO / ∆T = (IIO (Test 50 – IIO (Test 7)) / 80°C	GND	-28 V	GND	-2.5 V	GND	-28 V	GND	-2.5 V	GND	GND	Calculate value using data from tests 43 and 44	GND	GND	GND	GND	GND	GND	GND	GND
			1	30 V	2 V	5 V	2.5 V	AIC	30 V	2 V	5 V	2.5 V	30 V	2 <	5 V	2.5 V	30 V	5 V	Calculate	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V
	Test	Ou		48	49	50	51	52 <u>8</u> /	53	54	55	56	57	58	59	60	61		62 <u>4</u> /	63 <u>6</u> /	64 <u>7</u> /	65	66	67		68	
	MIL-STD	-883	method	4001	3	3	39	3	3	*	3	39	39	39	2	3	4003	*	4003	3011	3005	4004	39	ų	3	3	×
	Symbol			lıo				ΔΙΟ/ΔΤ	+lıB				-IB				+PSRR		CMR	los(+)	lcc	+VOP	-VOP	AVS(+)			
	Subgroup			3	TA =-55°C																	4	TA =	+25°C			

MIL-M-38510/110C TABLE III. <u>Group A inspection for device types 05 and 06</u> - Continued. <u>1</u>/

				1																							
	Unit			V/m/V	**	*	n	N/m	>	3	3	3	3	77	V/m/V	3	3	**	V/m/	3	3	**	л Ч	>	37	3	3
Device types	05, 06	Limits	Мах					35	1.5	0.4													35	1.5	0.4		
Device	05,	Lin	Min	10		10					27	2.4	27	26	25		25		10		10					27	2.4
		Equations <u>3</u> /		AVS(+) = 1.5/(E60 – E59)		AVS(-) = 1.5/(E62 – E61)		VOL = (E0)3	VOL = (E0)4	VOL = (E0)5	VOH = (E0)6	VOH = (E0)7	+VOP = (E0)8	-VOP = (E0)9	AVS(+) = 25/(E64 – E63)		AVS(+) = 15/(E66 – E65)		AVS = 1.5/(E68 – E67)		AVS = 1.5/(E70 – E69)		VOL = (E0)10	VOL = (E0)11	VOL = (E0)12	VOH = (E0)13	VOH = (E0)14
		ins	Unit	^	3	*	11	мV	>	15	a	3	59	4	15	39	31	99	2	3	*	16	m<	>	39	37	16
		Measured pins	Value	E59	E60	E61	E62	(E0)3	(E0)4	(E0)5	(E0)6	(E0)7	(E0)8	(E0)9	E63	E64	E65	E66	E67	E68	E69	E70	(E0)10	(E0)11	(E0)12	(E0)13	(E0)14
		Ŵ	No.	5	a	z	n	3	×	2	ä	2	z	n	5	z	z	3	z	z	z	u	с	z	z	2	'n
	Energized	relays <u>2</u> /		K8	K8	K7	K7	K11, K9	K11	K11	K11	K11	K8	K7	K8	K8	K7	K7	K8	K8	K7	K7	K11, K9	K11	K11	K11	K11
			5																								
	bers		4	-2.5 V	-1 V	-2.5 V	-1 V	5 V	5 V	5 V	-5 V	-5 V	-30 V	-30 V	-26 V	-1 <	-20 V	-5V	-2.5 V	-1 <	-2.5 V	-1 V	5 V	5 V	5 V	-5 V	-5 V
	Adapter pin numbers		3						5 mA	2 µA	-10 mA	-10 mA												5 mA	2 µA	-10 mA	-10 mA
	Adapte		2	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND
			1	5 V	5 V	5 V	5 V	30 V	30 V	4.5 V	30 V	4.5 V	30 V	30 V	30 V	30 V	30 V	30 V	5 <	5 V	5 V	5 V	30 V	30 V	4.5 V	30 V	4.5 V
	Test	.ou		69		70		71	72	73	74	75	76	77	78		79		80	-	81		82	83	84	85	86
	MIL-STD	-883	method	4004	ч	"	u	3007	3	3	3006	3006	4004	z	z	3	z	3	a	3	z	n	3007	3	n	3006	3006
	Symbol			AVS							МОН	ЧОН	+VOP	-VOP	AVS(+)				AVS				NOL			ЧОН	VOH
	Subgroup			4	TA =+25°C								5	TA =+125°C													

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

e iypeo	05, 06 Unit	Limits	Max	>	Λ	V/m/V	"	39	29	39	39	59	59	35 mV	1.5 V	0.4 "	31	31	15 μVrms	50 μVpk	dB		29	59	59	39		39
Device types	05,	Lir	Min	27	26	25	25	25	25	10		10					27	2.3			80	80	80	80	80	80	80	80
		Equations <u>3</u> /		+VOP = (E0)15	+VOP = (E0)16	AVS(+) = 25/(E72 – E71)		AVS(+) = 15/(E74 - E73)		AVS = 1.5/(E76 – E75)		AVS = 1.5/(E78 – E77)		VOL = (E0)17	VOL = (E0)18	VOL = (E0)19	VOH = (E0)20	VOH = (E0)21	NI(BB) = (E0)22	NI(PC) = (E0)23	$CS = 20 \log 4$	1.5 x 10 ['] / E79 – E80	$CS = 20 \log 4$	1.5 × 10 [^] / E81 – E82	$CS = 20 \log 4$	1.5 × 10 [^] / E83 – E84	CS = 20 log	1.5 x 10 ^{-/} E85 – E86
		pins	Unit	>	"	3	¥	3	3	3	3	3	**	٨	>	3	2	2	mVrms	mVpk	>	3	3	3	3	3	2	3
		Measured pins	Value	(E0)15	(E0)16	E71	E72	E73	E74	E75	E76	E77	E78	(E0)17	(E0)18	(E0)19	(E0)20	(E0)21	(E0)22	(E0)23	E79	E80	E81	E82	E83	E84	E85	Цор
		Σ	No.	з	"	5	"	"	"	**	n	ä	**	3	*	"	*	*	"	'n	5	"	"	"	"	"	ä	"
	Energized	relays <u>2</u> /		K8	K7	К8	K8	K7	K7	K8	K8	K7	K7	K11, K9	K11	K11	K11	K11	K10, K11	K5,K6,K10, K11	See fig. 3	и	и	n	и	и	×	'n
			5																									
	bers		4	-30 V	-30 V	-26 V	-1 V	-20 V	-5 V	-2.5 V	-1 V	-2.5 V	-1 V	5 V	5 V	5 V	-5 V	-5 V	GND	GND	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V
	Adapter pin numbers		3												5 mA	2 µA	-10 mA	-10 mA			16 V	1 V	16 V	1 V	16 V	1 /	16 V	1 <
	Adapte		2	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	-15 V	-15 V	GND	GND	GND	GND	GND	GND	GND	GND
			1	30 V	30 V	30 V	30 V	30 V	30 V	5 V	5 V	5 V	5 V	30 V	30 V	4.5 V	30 V	4.5 V	15 V	15 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V
	Test	no.		87	88	89		06		91		92		93	94	95	96	97	98 <u>10</u> /	99 <u>10</u> /	100		101		102		103	
	MIL-STD	-883	method	4004	3	3	2	3	3	z	3	×	n	3007	z	z	3006	3006										
	Symbol			+VOP	+VOP	AVS(+)				AVS				NOL			НОЛ	НОЛ	NI(BB)	NI(PC)	cs							
	Subgroup			9	TA =-55°C														7	TA =+25°C								

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

	Unit			dB	*	z	×	z	z	z	z	3	3	3	3	3	3	3	з	sni	%	V/µs	V/µs	
types	35	lts	Мах																	1.0	60			
Device types	05, 05	Limits	Min	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80			0.1	0.1	
		Equations $3/$		$CS = 20 \log 4$	1.5 × 10 / E87 – E88	$CS = 20 \log 4$	1.5 x 10 ⁷ / E89 – E90	$CS = 20 \log \frac{1}{4}$	1.5 x 10 ⁻ / E91 – E92	CS = 20 log	1.5 x 10 ⁻ / E93 – E94	$CS = 20 \log_{10}^{10}$	1.5 X 10 / E95 - E96	$CS = 20 \log^{-1}{100}$	11.9 X 10 / E9/ - E98	CS = 20 log	1.5 X 10 / E99 - E100	$CS = 20 \log_{10} \frac{4}{1000}$	11.3 × 10 / E101 - E102	(Waveform 1) TR(t_{f}) = Δt	(Waveform 1) TR(OS) = 100 (∆VO/VO)	(Waveform 2) SR(+) = VO/∆t	(Waveform 3) SR(-) = $\Delta VO/\Delta t$	Same tests, terminal conditions and limits as subgroup 7, tests 112 through 115 except TA = 125° C and TA = -55° C.
		IS	Unit	^	3	3	33	3	з	39	33	3	33	3	33	3	3	3	3	sri	^	V; µs	V; µs	except TA
		Measured pins	Value	E87	E88	E89	E90	E91	E92	E93	E94	E95	E96	E97	E98	E99	E100	E101	E102	Δt	ΟΛΔ;ΟΥ	ΔVO; Δt	ΔVO; Δt	through 115
			No.	5			•	•																ests 112
	Energized	relays <u>2</u> /		See fig. 3	3	3	3	3	3	3	3	3	3	3	3	3	z	3	3	See fig. 4	3	3	3	ubgroup 7, t
			5																	оит	OUT	OUT	OUT	imits as s
	nbers		4	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V	-1.4 V					ions and
	Adapter pin numbers		3	16 V	1 <	16 V	1 <	16 V	1 <	16 V	1 V	16 V	1 V	16 V	1 V	16 V	1 V	16 V	1 V	Z	Z	Z	Z	al condit
	Adapt		2	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	sts, termir
			1	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	30 V	Same te
	Test	no.		104		105		106		107		108		109		110		111		112	113	114	115	116 to 123
	MIL-STD	-883	method																			4002	3	
	Symbol			cs																TR(tr)	TR(os)	SR(+)	SR(-)	
	Subgroup			7	TA =+25°C																			8

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

TABLE III. Group A inspection - Continued.

1/ Use table III in conjunction with the following:

Tests	Device type	<u>Figure</u>
1 – 102	01 – 04	2
1 – 99	05 - 06	
103 – 114	01 – 04	3
100 – 111	05 - 06	
115 – 126	01 – 04	4
112 - 123	05 - 06	

- 2/ K1, K2, K3, or K4 relay will also be energized as follows:
 - a. Device types 01 through 04 test numbers 22 and 103 through 126.
 - b. Device types 05 and 06 test numbers 20 and 100 through 123.
- 3/ The equations take into account both the closed loop gain of 1,000 and the scale factor multiplier so that the calculator value is in table I units; therefore, use the measured value units in the equation. (For example: If E₁ = 2 V and V_{IO} = E₁, then V_{IO} = E₁, then V_{IO} = 2 mV).
- <u>4</u>/ Each device shall be tested over the common mode range as specified in table III with the output forced to the worse case condition. V_{CM} is achieved by grounding the inputs and algebraically subtracting V_{CM} from each supply. Common mode rejection is calculated using the offset voltage values measured at the common mode range end points.
- <u>5</u>/ In device types 01 through 04, to minimize thermal drift, the reference voltage for gain measurement (E₃, E₂₁, and E₃₉) shall be taken immediately prior to or after the reading corresponding to device gain (E₅₅, E₅₆, E₅₇, E₅₈, E₆₃, E₆₄, E₆₅, E₆₆, E₇₁, E₇₂, E₇₃, and E₇₄).
- 6/ Only one amplifier shall be tested at one time and its output shall be shorted to ground for 25 ms or less.
- <u>7</u>/ Each amplifier shall be tested separately, except for the I_{CC} measurements where all the amplifiers shall be connected as grounded followers (relays K1 through K4 de-energized).
- 8/ Tests 27, 32, 51, and 56 for devices types 01 through 04 and tests 25, 30, 47, and 52 for device types 05 and 06, which require a read and record measurement plus a calculation, may be omitted except when subgroups 2 and 3 are being accomplished for group A sampling inspection and groups C and D end point measurement.
- 9/ SR(+) and SR(-) are 0.2 V/µs for device type 01 and 0.8 V/µs for device type 02.
- 10/ Broadband noise (NI(BB) shall be measured using an rms voltmeter with a bandwidth of 10 Hz to 5 kHz. "Popcorn" noise (NI(PC)) shall be measured for 15 seconds.
- <u>11</u>/ For device types 01, 03, and 04, V_{IN} = 10 V; for device type 02, V_{IN} = 2 V.
- <u>12</u>/ For device types 01, 03, and 04, V_{IN} = -10 V; for device type 02, V_{IN} = -2 V.

TABLE IV. Group C and Group B life test end point electrical parameters.

$(T_A = +25^{\circ}C, \pm V_{CC} = \pm 20 \text{ V} \text{ for device types } 01 - 04 \text{ and}$
$+V_{CC} = 30$ V for device types 05 and 06).

Table III test no.	Test		01,	02			0	3		Unit
		Lir	nit	De	elta	Lir	nit	De	elta	
		Min	Max	Min	Max	Min	Max	Min	Max	
3	VIO	-5	+5	-1	+1	-3.0	+3.0	-0.5	+0.5	mV
11	+l _{IB}	+0.1	+100	-15	+15	-200	-1	-20	20	nA
15	-I _{IB}	+0.1	+100	-15	+15	-200	-1	-20	20	nA

Table III test no.	Test		0	4			0	5		Unit
		Lir	nit	De	elta	Lir	nit	De	elta	
		Min	Max	Min	Max	Min	Max	Min	Max	
3	VIO	-5	+5	-1	+1	-5	+5	-1	+1	mV
11	+I _{IB}	-250	-1	-25	+25	-150	-1	-15	+15	nA
15	-I _{IB}	-250	-1	-25	+25	-150	-1	-15	+15	nA

Table III test no.	Test		Unit			
		Limit		Delta		
		Min	Max	Min	Max	
3	VIO	-2	+2	-0.5	+0.5	mV
11	+I _{IB}	-50	-1	-10	+10	nA
15	-I _{IB}	-50	-1	-10	+10	nA

 $\underline{1}$ / For device types 05 and 06, the table III test numbers are as follows: V_{IO} use test number 1, +I_{IB} use the test number 9, -I_{IB} use test number 13.

4.4 <u>Technology Conformance inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Tests shall be as specified in table II herein.
- b. Subgroups 9, 10, and 11 shall be omitted.

4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.

4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

- a. End point electrical parameters shall be as specified in table II herein.
- b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End point electrical parameters shall be as specified in table II herein.

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified and as follows.

4.5.1 <u>Voltage and current</u>. All voltage values given are referenced to the external zero reference level of the supply voltage. Currents given are for conventional current and are positive when flowing into the referenced terminal.

4.5.2 <u>Life test cooldown procedure</u>. When devices are measured at +25°C following application of the steady state life or burn-in test condition, they shall be cooled to within 10°C of their power stable condition at room temperature prior to removal of the bias.

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this specification are intended for Government microcircuit applications (original equipment) and logistic purposes.

- 6.2 <u>Ordering data</u>. The contract or purchase order should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to acquiring activity in addition to notification of the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of MIL-STD-883, method 5003), corrective action and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - i. Requirements for "JAN" marking.
 - j. Packaging requirements (see 5.1).

6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43213-1199.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-STD-1331.

6.6 Logistic support. Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired to Government logistic support will be acquired to device class B (see 1.2.2), and lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.

6.7 <u>Substitutability</u>. The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-M-38535.

Military device type	Generic-industry type
01	LM148
02	LM149
03	4741, 4156
04	4136
05	LM124
06	LM124A

6.7 <u>Changes from previous issue</u>. Asterisks are not used in this revision to identify changes with respect to the previous issue, due to the extensiveness of the changes.

Custodians: Army - CR Navy - EC Air Force - 11 NASA - NA DLA - CC Preparing activity: DLA - CC

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3. The preparing activity must provide a re	ply within 30 days from receipt of the forn	n.			
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3. DOCUMENT TITLE					
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4. NATURE OF CHANGE (Identify paragraph	oh number and include proposed rewrite,	if possible. Attach extra sheets as needed.)			
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